

# IGBT Modules

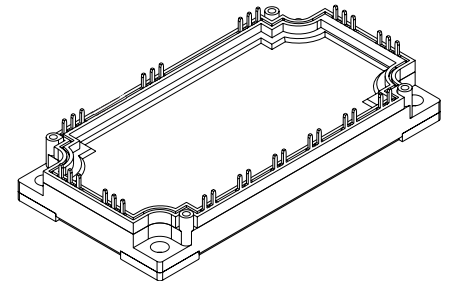
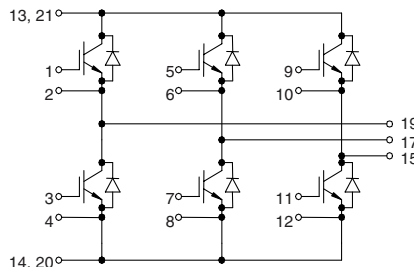
## Sixpack

Short Circuit SOA Capability  
Square RBSOA

$$I_{C25} = 225 \text{ A}$$

$$V_{CES} = 600 \text{ V}$$

$$V_{CE(sat) \text{ typ.}} = 2.0 \text{ V}$$



### IGBTs

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
$V_{GES}$		$\pm 20$	V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	225	A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	155	A
<b>RBSOA</b>	$V_{GE} = \pm 15 \text{ V}; R_G = 1.5 \Omega; T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100 \mu\text{H}$	$I_{CM} = 400$ $V_{CEK} \leq V_{CES}$	A
$t_{SC}$ <b>(SCSOA)</b>	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 1.5 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	675	W

### Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

### Advantages

- space savings
- reduced protection circuits
- package designed for wave soldering

### Typical Applications

- AC motor control
- AC servo and robot drives
- power supplies

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 200 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.0 2.3	V V	
$V_{GE(th)}$	$I_C = 4 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
$I_{CES}$	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.5	1.8 mA mA	
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			400 nA	
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 200 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 1.5 \Omega$		180 50 300 40 4.6 6.3	ns ns ns ns mJ mJ	
$C_{ies}$		$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		9.0	nF
$Q_{Gon}$		$V_{CE} = 300 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 200 \text{ A}$		670	nC
$R_{thJC}$		(per IGBT)			0.18 K/W

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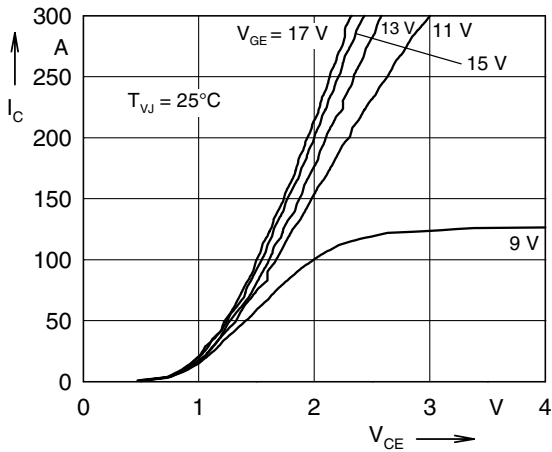


Fig. 1 Typ. output characteristics

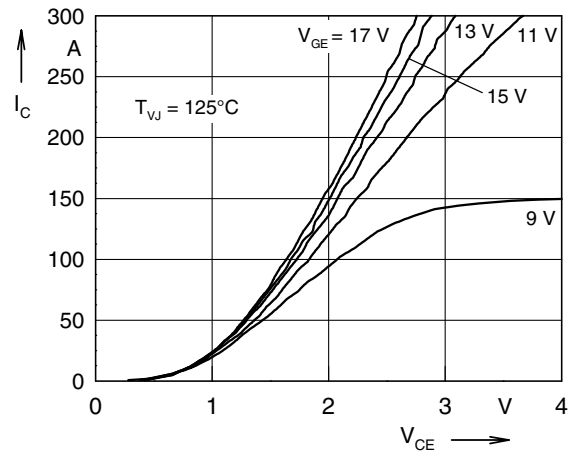


Fig. 2 Typ. output characteristics

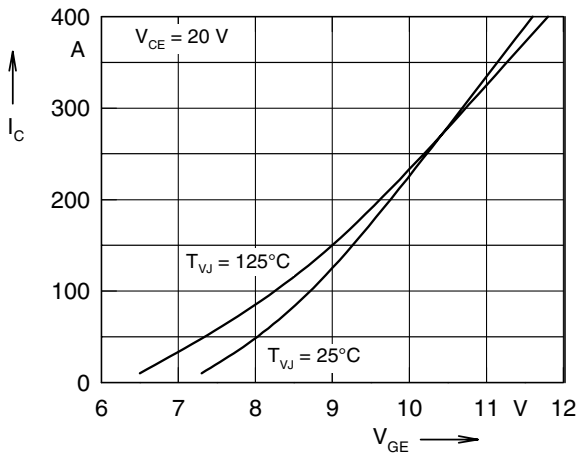


Fig. 3 Typ. transfer characteristics

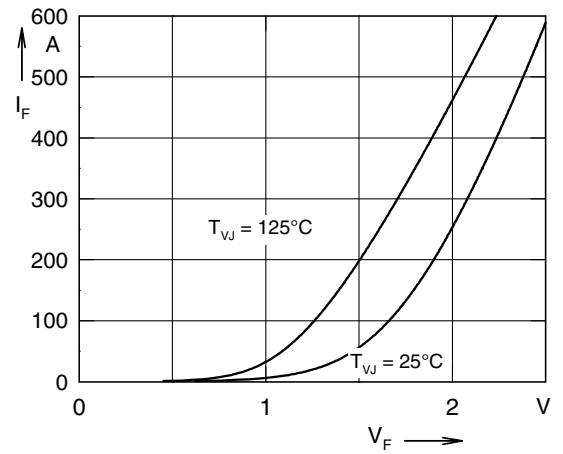


Fig. 4 Typ. forward characteristics of free wheeling diode

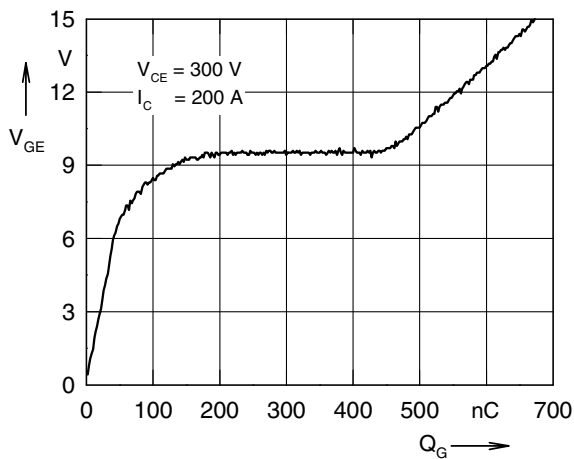


Fig. 5 Typ. turn on gate charge

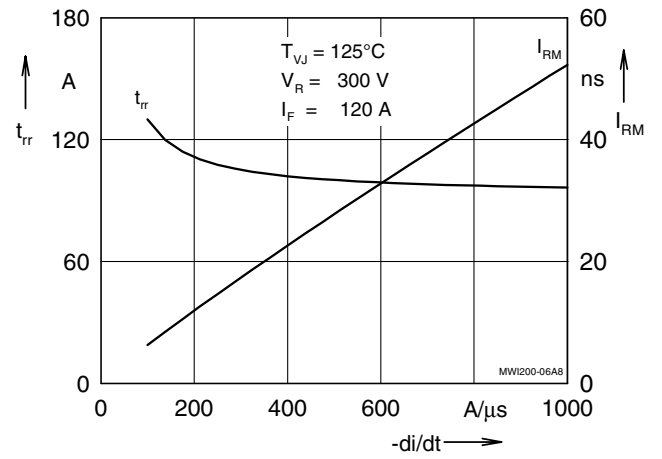


Fig. 6 Typ. turn off characteristics of free wheeling diode

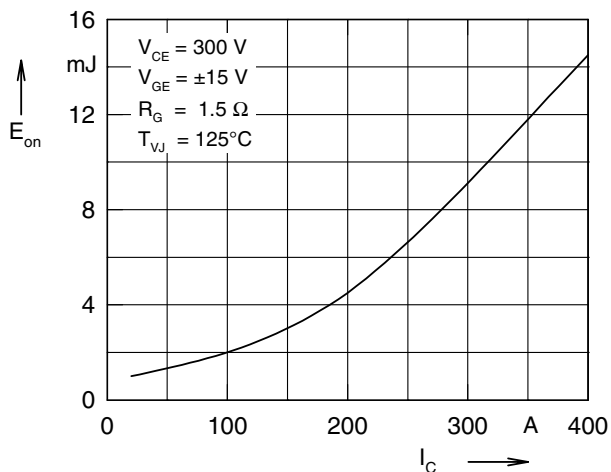


Fig. 7 Typ. turn on energy versus collector current

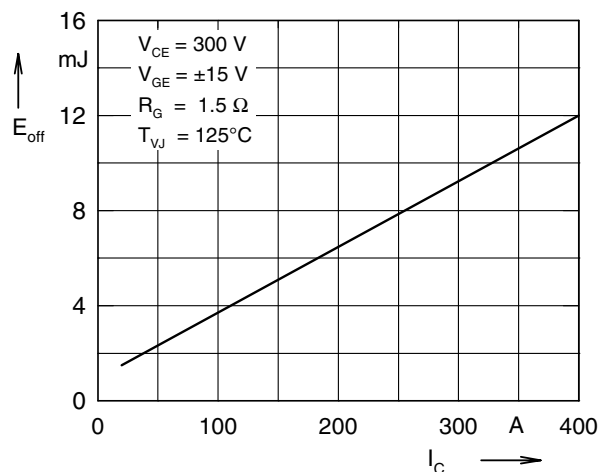


Fig. 8 Typ. turn off energy versus collector current

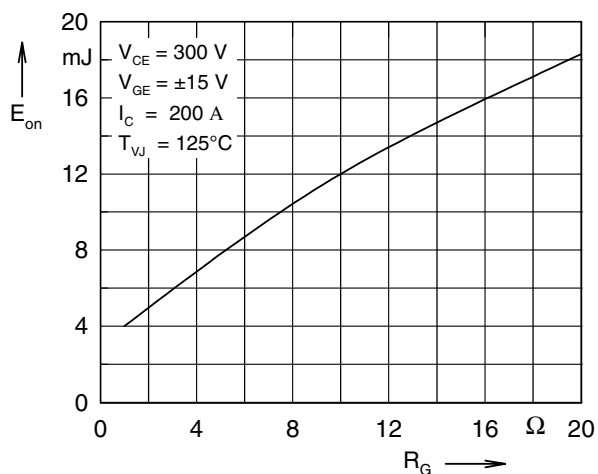


Fig. 9 Typ. turn on energy versus gate resistor

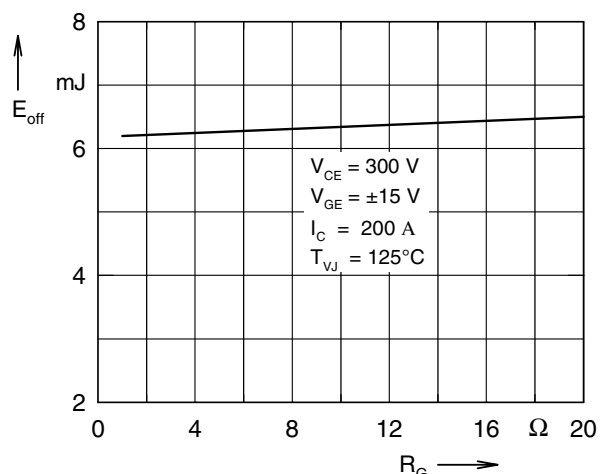


Fig.10 Typ. turn off energy versus gate resistor

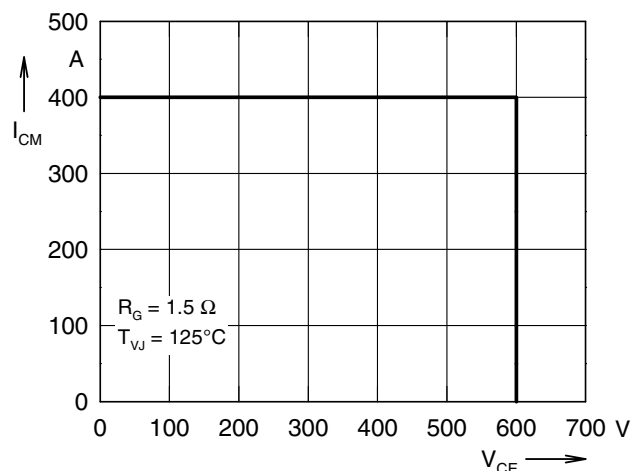


Fig. 11 Reverse biased safe operating area RBSOA

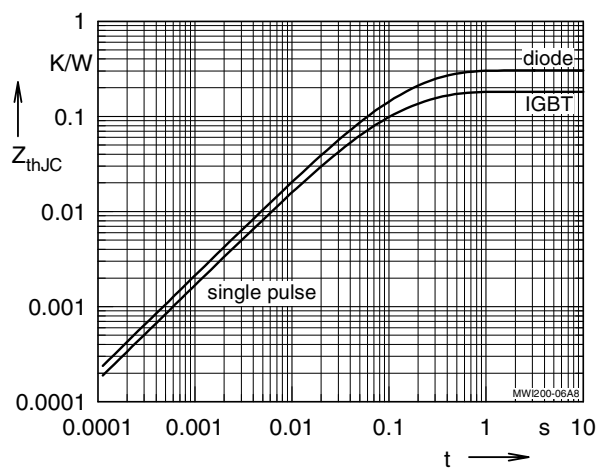


Fig. 12 Typ. transient thermal impedance